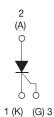


Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 40 A





1.45 V

150 mA

-40 °C to +125 °C

**TO-247AC** 

 $V_{\text{TM}}$ 

 $I_{\text{GT}}$ 

 $T_{J}$ 

 PRODUCT SUMMARY

 Package
 TO-247AC

 Diode variation
 Single SCR

 I<sub>T(AV)</sub>
 35 A

 V<sub>DRM</sub>/V<sub>RRM</sub>
 800 V, 1200 V

# Ť,

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- Low I<sub>GT</sub> parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





COMPLIANT
HALOGEN
FREE

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

#### **DESCRIPTION**

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I <sub>T(AV)</sub>	Sinusoidal waveform	35	- A				
I <sub>RMS</sub>		55					
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V				
I <sub>TSM</sub>		600	А				
V <sub>T</sub>	40 A, T <sub>J</sub> = 25 °C	1.45	V				
dV/dt		1000	V/µs				
dl/dt		100	A/µs				
T <sub>J</sub>		-40 to +125	°C				

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-40TPS08APbF, VS-40TPS08A-M3	800	900						
VS-40TPS08PbF, VS-40TPS08-M3	800	900	10					
VS-40TPS12APbF, VS-40TPS12A-M3	1200	1300	10					
VS-40TPS12PbF, VS-40TPS12-M3	1200	1300						



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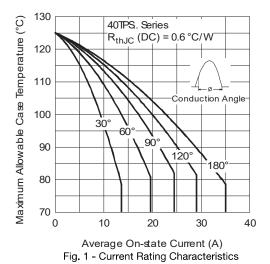
<b>ABSOLUTE MAXIMUM RATINGS</b>	,					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 79 °C, 180° conduction half sine wav	35			
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>		55	A		
Maximum peak, one-cycle	<b>I</b>	10 ms sine pulse, rated V <sub>RRM</sub> applied		500		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied		600		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	Initial $T_{.1} = T_{.1} \text{ max.}$	1250	A <sup>2</sup> s	
Maximum I-t for fusing		10 ms sine pulse, no voltage reapplied		1760		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied	17 600	A²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>		1.02	V		
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 405 %	1.23			
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C	9.74	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>		7.50			
Maximum peak on-state voltage	V <sub>TM</sub>	110 A, T <sub>J</sub> = 25 °C		1.85	V	
Maximum rate of rise of turned-on current	dI/dt	T <sub>J</sub> = 25 °C		100	A/µs	
Maximum holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial T	<sub>I</sub> = 1 A, <b>I</b> <sub>T</sub> = 25 °C	200		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C				
		T <sub>J</sub> = 25 °C	0.5	mA		
Maximum reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	$V_R = Rated V_{RRM}/V_E$	10			
Maximum rate of rise of off-state voltage 40TPS12A	.0.77.11	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$ - $k = 100 \Omega$			\// ·	
Maximum rate of rise of off-state voltage 40TPS12	- dV/dt				V/µs	

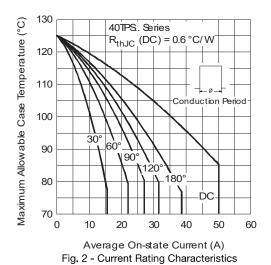
TRIGGERING						
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS		
Maximum peak gate power	P <sub>GM</sub>			10	W	
Maximum average gate power	P <sub>G(AV)</sub>			2.5	VV	
Maximum peak gate current	I <sub>GM</sub>			2.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	V	
		T <sub>J</sub> = - 40 °C		4.0		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	2.5	V	
		T <sub>J</sub> = 125 °C	resistive load	1.7		
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		270		
Maying up up wised DC grate as weath to trib age		T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	150	mA	
Maximum required DC gate current to trigger		T <sub>J</sub> = 125 °C	resistive load	80		
		$T_J = 25$ °C, for 40TPS08AP	40			
Maximum DC gate voltage not to trigger for 40TPS12	$V_{GD}$			0.25	٧	
Maximum DC gate current not to trigger for 40TPS12	I <sub>GD</sub>	$T_J = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated}$	6	mA		
Maximum DC gate voltage not to trigger for 40TPS12A	V <sub>GD</sub>	T 105 °C V Poted	0.15	V		
Maximum DC gate current not to trigger for 40TPS12A	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		1	mA	



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THERMAL AND MECHANICA	L SPECIFI	CATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC anavation	0.6			
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>	DC operation	40	°C/W		
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2			
A new publication was related			6	g		
Approximate weight			0.21	oz.		
minimum			6 (5)	kgf · cm		
Mounting torque maximum			12 (10)	(lbf ⋅ in)		
			40TP	S08A		
		0 11 70 04740	40TP	S12A		
Marking device		Case style TO-247AC	40TF	40TPS08		
				40TPS12		









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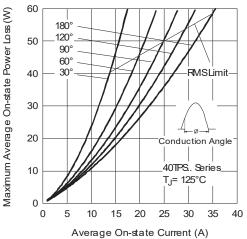
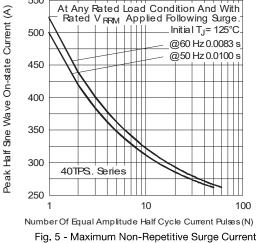


Fig. 3 - On-State Power Loss Characteristics



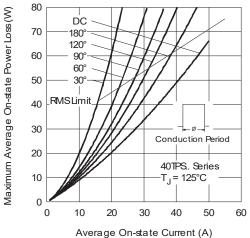


Fig. 4 - On-State Power Loss Characteristics

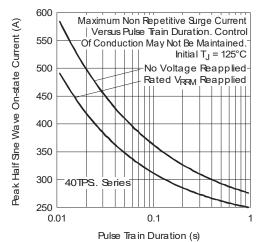


Fig. 6 - Maximum Non-Repetitive Surge Current

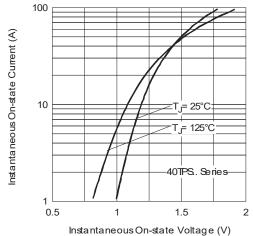


Fig. 7 - On-State Voltage Drop Characteristics

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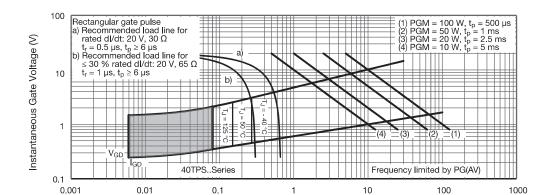


Fig. 8 - Gate Characteristics

Instantaneous Gate Current (A)

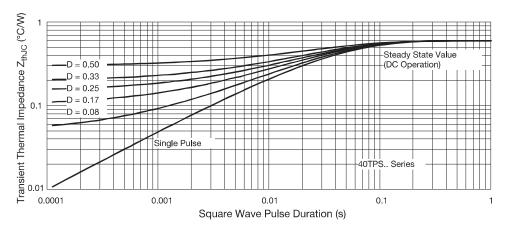
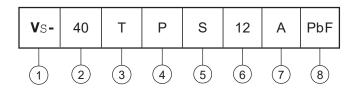


Fig. 9 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

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#### **ORDERING INFORMATION TABLE**

Device code



Vishay Semiconductors product

Current rating (40 = 40 A)

Circuit configuration:

T = Thyristor

4 Package:

P = TO-247

5 Type of silicon:

S = Standard recovery rectifier

08 = 800 V

Voltage ratings

12 = 1200 V

• A = Low lgt selection 40 mA maximum

• None = Standard Igt selection

8 Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-40TPS08APbF	25	500	Antistatic plastic tubes						
VS-40TPS08A-M3	25	500	Antistatic plastic tubes						
VS-40TPS08PbF	25	500	Antistatic plastic tubes						
VS-40TPS08-M3	25	500	Antistatic plastic tubes						
VS-40TPS12APbF	25	500	Antistatic plastic tubes						
VS-40TPS12A-M3	25	500	Antistatic plastic tubes						
VS-40TPS12PbF	25	500	Antistatic plastic tubes						
VS-40TPS12-M3	25	500	Antistatic plastic tubes						

LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95542				
Dout moding information	TO-247AC PbF	www.vishay.com/doc?95226				
Part marking information	TO-247AC-M3	www.vishay.com/doc?95007				



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NOTES

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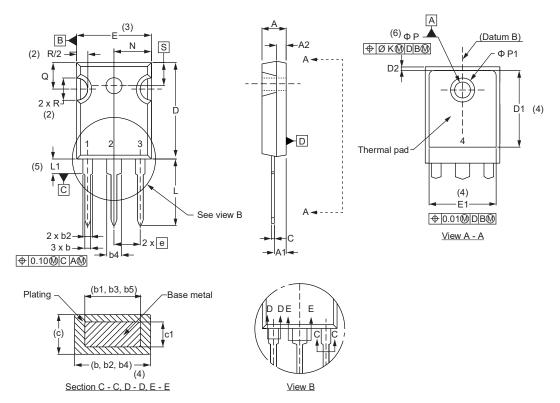
MAX. 0.053 0.625

0.634 0.169

0.144 0.291 0.224 0.216

### TO-247 - 50 mils L/F

#### DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		ICHES NOTES		SYMBOL		MILLIMETERS		INCHES	
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIBOL	MIN.	MAX.	MIN.	MAX
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.05
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.62
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-
b	0.99	1.40	0.039	0.055			е	5.46 BSC		0.215	BSC
b1	0.99	1.35	0.039	0.053			Ø K 0.254		0.254		)10
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.63
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.16
b4	2.59	3.43	0.102	0.135			N	7.62 BSC		0	.3
b5	2.59	3.38	0.102	0.133			ØР	3.56	3.66	0.14	0.14
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.29
с1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.22
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.21
D1	13.08	-	0.515	-	4		S	5.51 BSC		0.217	BSC

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q

Revision: 21-Apr-15 Document Number: 95542



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